

Technical Data

DIODE



maximum ratings

Voltage, Reverse (VR)	400.0	V	NO.	1N5616-M
Voltage, Reverse Peak (VRM)	400.0	V	TYPE	SILICON
Current at VR = 0V (IO)		A		RECTIFIER
Current Average Rectified (IF)	1.0	A		
Current Surge Peak (IFM)		A	CASE	SOD-57
Current, Surge (IFM) at tp = 10 ms	50.0	A		MIL-S-19500
Max. Power Dissipation (PT) at TC = 25 °C		W		BURN-IN 48h/125°C
Max. Thermal Resistance (Rth J-A)	50.0	°C/W		
Max. Junction Temperature (TJ)	200.0	°C		

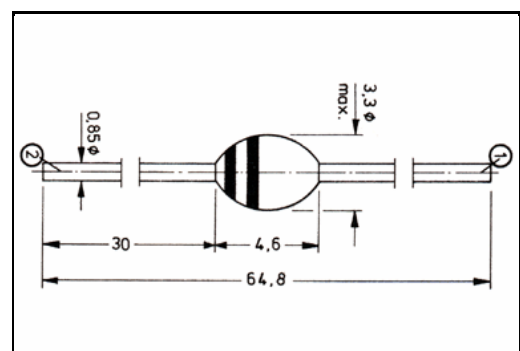
PERFORMANCE CHARACTERISTICS at $T_c = 25^\circ\text{C}$, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	VF	IF = 1.0 A (1)	-	1.2	V
2.	IR	VR = 400.0 V	-	0.5	μA
3.	IR	VR = 400.0 V, TA = 100.0 °C	-	25.0	μA
4.	trr	IF = 0.5 A, IR = 1.0 A, irr = 0.25 A	-	2.0	μs
5.	CT	VR = 12.0 V, f = 1.0 MHz	-	50.0	pF
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Notes

(1)pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$

DIMENSIONS
in mm



Marking 5616-M+GREEN DOT
Customer GENERAL PURPOSE